Project and Thesis Folder 2021

- Pillars of the Institute for Microelectronics
 - Teaching: Programming in C and C++
 - Simulation: Numerical simulation of semiconductor devices and processes
 - Experimental: Development of characterization equipment and techniques
- Unique chance to improve teaching quality and scientific research
- Potential to earn some extra money: Geringfügige Beschäftigung
- Optional seminars and practical courses:
 - 360.238 Experimental Device Characterization in Microelectronics
 - 360.230 Emerging Devices
 - 360.206 Programming
- Bachelor Thesis
- Master Thesis



Numerical Solvers for Diffusion Equations (using Python)



Supervisor:

Luiz Felipe Aguinsky

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Project LA1

- One crucial challenge in the production of high aspect ratio (HAR) structures is the depletion of etchant/depositant species at the bottom
- One approach to model neutral species (e.g. ALD precursors) is using Knudsen diffusion
- When the Knudsen approach is extended to take into account arbitrary geometries, we encounter a system of coupled ODEs

Tasks:

- Implement a framework to test different ODE system solvers
- Investigate the impact of each computational method
- Compare to available Monte Carlo and radiosity models

- Numerical methods for ODE (Runge-Kutta, Euler, ...)
- Experience with Python/SciPy is a plus
- Familiarity with semiconductor processing is NOT necessary



Optimization of Plasma Etching Simulations



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Project LA2

- Plasma etching simulations have many free parameters
- Mapping these parameters to experimental inputs is not straightforward
- Computational optimization of the parameters is a key approach

Tasks:

- Explore optimizers to calibrate the simulations to available experimental data
- Develop a methodology to use the calibrated simulations to optimize fabrication figures of merit





- Programming in C/C++ or Python
- Familiarity with semiconductor processing is NOT necessary



Modeling of Atomic Layer Deposition (ALD)



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Project LA3

- ALD is a crucial step in modern semiconductor fabrication
- The fundamental aspect of ALD is that the films grown by it show self-limiting behavior
- This type of growth is not directly available from Level-set based simulators

Tasks:

- Develop a mathematical model for self-limiting growth within the Level-set method
- Implement this model in an existing simulator

- Programming in C++
- Knowledge of Finite Differences is a plus
- Familiarity with semiconductor processing is NOT necessary





Absence and Leave Management System

Months, Start with 2 V 2019 V SHOW ME!

September 2018 Visit Holiday

Previous

(instructions)

Next Group default 🗸



Supervisor:

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Project JC1

- Web-based holiday and absence planner application is desired
- It should be viewable and acccesible from everywhere
- Adapt to the existing design of the IuE hompage
- A standalone tool is desired

Tasks:

- Implement a simple leave management system
- User access rights should be made simple
- Primary calendar view should be one month
- Responsive design

- Webpage and database programming
- HTML, CSS, Python/Perl/Java (open source, no restrictions)
- Some knowledge in graphic conceptualization and design desired

Web-based Interactive Slide Development



Supervisor:

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Project TE1

- Reveal.JS offers interactive, web based presentations
- The IuE is developing set of interactive slide templates
- Design engaging, interactive elements using web development tools



- Fine-tune the presentation template
- Implement responsive version of the slides
- Design system to serve uploaded slides
- Create new components in line with existing style

Required knowledge:

• HTML, CSS, Javascript or a desire to learn them





Characterization of the Gas Sensing Capability of 2D Materials



Supervisor:

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Project LF1

- 2D materials such as the graphene family of materials (graphene, graphene oxide, etc.) and MoS₂ have shown potential for use as a gas sensor
- Combined characterizations and modeling are essential in order to better understand the capabilities of these films for sensing

Tasks:

- Perform characterizations of the electrical behavior of several devices under varying ambient conditions
- Write scripts to control the measurement setup

- Basic knowledge of Python
- Interest in sensor physics



Simulate Sensors Based on 2D Materials



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Project LF2

- 2D materials are heavily investigated for their application in disease detection, both as biosensors and gas sensors
- Simulation of such devices helps to understand the novel materials and to design novel sensor applications

Tasks:

Required knowledge:

Programming (Python, C, C++)

• (Rudimentary) understanding and

- Perform simulations on bio-sensors or gas sensors which are based on 2D materials
- Compare and improve models by calibrating to measurements

profound interest in semiconductor physics

Reference Electrode

target

biomolecules

Electrolyte

receptor

gate

dielectric

molecules



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Physical Modeling of Novel Semiconductor Devices



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Project LF3

To investigate new devices, based on novel materials such as 2D materials and Perovskites, physical modeling tools are essential

• We are developing a framework in C++ to model electron transport in semiconductors under various scattering phenomena

Tasks:

 Implement models for different types of electron scattering mechanisms in C++

- Programming in C++
- (Rudimentary) understanding and profound interest in semiconductor physics





- -Secondary Electron Path
- Characteristic X-Ray

Modeling Electromigration in Platinum Microheaters



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Project LF4

 Microheaters are frequently used for sensor structures to heat up the sensing layer

- The heat provides enough energy to activate the sensing interaction between ambient molecules and sensing film
- The microheater can frequently fail due to applied heating/cooling cycles and operation at high temperature due to electromigration

Tasks:

- A model for electromigration is already provided and is frequently applied to copper lines
- The tasks are to modify the model for platinum and test it on common microheater geometries

Required knowledge:

 Some knowledge in electro-thermo-mechanical simulations is helpful, but not essential



Modeling Electron Transport in Metals



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Project LF5

• A software tool written in C can track how electrons move in different materials, such as silicon or copper

- Metals are of particular interest due to the added scattering off of grain boundaries
- The software is currently a small part in a larger code framework, but we want to make it an independent code



5.8×10

5.6×10

potential.csv* using 1:

Required knowledge:

Tasks:

- Programming in C or C++
- Some knowledge in metal microstructure and conductivity



Hot-Carrier Degradation (HCD)



Supervisor:

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Project MJ1

 Charge carriers in the channel can gain high kinetic energy and trigger the creation of defects at the Si/SiO₂ interface

- To understand how carriers are distributed over energy (energy distribution function), a full solution of the Boltzmann transport equation is needed
- Combining a physics-based model and a state of the art device simulator enables us to gain insight into this degradation phenomenon

Possible Tasks:

- Experimental characterization
 (e.g. the variability, different exp. methods)
- Modeling of HCD related phenomena
- Development of physics-based model

- Programming with Python/C++
- (Basic) knowledge of device simulations
- Interest in physics







Interplay of Degradation Mechanisms



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Project MJ2

- Bias Temperature Instability (BTI) and Hot Carrier Degradation (HCD) are two major device reliability issues
- However, both degradation modes are generally described and characterized independently
- We aim to understand and model the interplay between BTI and HCD

Possible Tasks:

- Experimental characterization
- (e.g. stress maps over bias space)
- (Improve) Modeling of degradation phenomena

- Programming with C++/Python
- (Basic) knowledge of device simulations
- Interest in experimental work





Atomistic Simulations



Supervisor:

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Project MJ3

- Ab-initio simulations on an atomistic level are needed to identify the properties of defects
- In this context, Density Functional Theory (DFT) is used to calculate e.g. the energetic position of defects, activation energies, ...

Possible Tasks:

- Characterize realistic interface structures (e.g. Si/SiO₂)
- Characterize new and emerging technologies and materials
- Explore new simulation approaches

- Solid knowledge/interest in physics
- Postprocessing data (bash/python/...)



Simulation Framework



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Project MJ4

- Analysis of differential equation systems using numerical methods (e.g. spatial and time discretization schemes)
- Simulation of semiconductor devices
 - Drift-diffusion model
 - Modeling of physical parameters

Possible Tasks:

- Development a new simulation framework
- (preferable) Python based using existing libraries

Required knowledge:

- Good knowledge of device simulations (MEB)
- Programming with Python
- Interest in numerics

 $\nabla^{2}\psi = q(n - p - C)/\varepsilon$ $\nabla \cdot (\mu_{n}n\nabla\psi - \mu_{n}V_{T}\nabla n) + \frac{\partial n}{\partial t} = -R ,$ $\nabla \cdot (\mu_{p}p\nabla\psi + \mu_{p}V_{T}\nabla p) - \frac{\partial p}{\partial t} = R .$ 5 point discretization





Band Structure Calculation for Silicon Carbide



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Project MK1

- Silicon Carbide (SiC) is a wide bandgap material often used in modern power devices
- Knowledge of the electronic band structure is important in order to understand carrier mobility and device performance
- The aim of this project is to extend an existing band structure code which assumes a cubic lattice to the hexagonal lattice of SiC

Tasks:

- Augment the empirical pseudopotential code (EPM) to deal with the Wurtzite lattice
- Verify already published fitting-factors for SiC
- Compare the results with data from literature

Requirements:

- Programming in C
- Interest in semiconductor physics



Automatic Python Wrapper for C++ projects



Supervisor:

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Project XK1

- Semiconductor process simulations require high performance implementations for reasonable runtimes (so not in python, but C or C++)
- Using C/C++ libraries can be complex
- Wrapping such simulators as python libraries makes them accessible to a wide audience, without the need to understand everything the library does

Usability of C++ / Python:



Choose your enemy



Tasks:

- Wrap a large C++ project with the necessary interfacing code to expose it to the python language
- Develope a C++ parser, which does this automatically for any project

Required knowledge:

Programming in C++

Build a Parameter Parser for ViennaTS



Supervisor:

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Project XK2

- ViennaTS is a process simulation tool used to model semiconductor fabrication steps
- Currently only text based parsing

Required knowledge:

• Programming in C++

 Especially web technology relies on JSON formatted data for its robustness

Tasks:

 Redesign the way information is passed to the simulator and implement a JSON based parameter input with automatic input checks





tatistical_accuracy=10000 in_ion_energy=50; rlta_ion_energy=40; lux ion=1.5e15;

lux polymer=4.5e15

del_name="HBr_O2PlasmaEtching" tive_layers={5,6}; sk layers = {4};

direction={1,0,0}

statistical accuracy=10000



(a) Epitaxial growth and (b) Dummy gate patterning. double patterning.

(c) Spacer formation and patterning.

Plain Text + Tab Width: 8 + Lo 52, Col 9 + INS







(d) Source/drain epitaxy. (e) Channel release.

(f) Final geometry after gate material deposition.

Ray Tracer for ViennaTS



Supervisor:

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Project XK3

- Recently, the ViennaTS codebase was modernised. The ray tracer is not refactored yet
- Although the ray tracer is powerful, it is hard to maintain and adapt, because of its unclean interfaces
- Great project to learn about fundamentals of ray tracing engines as used in graphics applications

Tasks:

 Re-implement the ray tracer as a standalone library for modern use and develop clean and portable interfaces.

Required knowledge:

Advanced Knowledge of C++

Without Ray Tracing:



With Ray Tracing:



Surface Advancement using Task Multithreading



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Project XK4

- ViennaLS is a level set engine for describing surfaces during micro-processor fabrication; The same concept is used by Disney / Pixar for animation films
- We have developed a fast algorithm for computing surface movement over large distances
- This algorithm could be even faster using a tasking approach for multithreading with each thread doing calculations, once it is available until all calculations are done



Tasks:

- Refactor the algorithm to allow for this new approach
- Distribute work across threads

Required knowledge:

Advanced Knowledge of C++



Modeling of MOSFETs based on 2D Materials



Supervisor:

Theresia Knobloch

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Project TK1

• Benchmarking of different approaches

- TCAD vs. compact model
- scattering dominated vs. ballistic
- Calibrate the models to measurement data

Tasks:

- Simulate transfer characteristics with 2 models
- Compare the simulation to measurement data
- Interpret observed differences

- Programming skills (Python)
- Profound physical understanding
- ev. Circuit modeling skills (HSPICE, Verilog-A)



3D Printing of FET Models



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Project TK2

- Drawing 3D models of a FinFET in a CAD-tool
- Disassemble the model into individual components
 - parts should form a 3D puzzle
- 3D Printing of the components

Tasks:

- Draw a 3D CAD model
- 3D Printing of the puzzle components
- User manual for didactic purposes

- 3D Modeling experience (FreeCAD, Blender, ...)
- ev. Experience with 3D printing



Algorithm for Electron-Electron Scattering in Monte Carlo Device Simulation



Supervisor:

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Project HK1

- Hot carriers occuring in integrated transistors cause a degradation of the electrical characteristics
- Understanding on this degradation effect requires knowledge of the energy distribution of the carriers
 - This distribution is strongly affected by electron scattering (EES)
- The aim of this work is to implement a novel algorithm for EES in the Vienna Monte Carlo (VMC) simulator

Possible Tasks:

- Implement a recently developed algorithm for EES in the VMC simulator
- Test the implementation against other models and implementations

Required knowledge:

- Programming in C
- Interest in semiconductor physics

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Simulate Large Structures using ViennaLS



Supervisor:

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Project PM1

- ViennaLS is a high-performance level set engine tailored towards micro-electronic fabrication simulations
- Its full capabilities have not yet been explored on a modern high performance computer
- Simulations of even large ICs should be possible

Tasks:

 Benchmark large scale simulations using ViennaLS on our new high performance cluster (2x 20 Cores, 768GB RAM)

Required knowledge:

• Advanced Knowledge of C++



Domain Decomposition for Parallel Velocity Extension



Supervisor:

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Project MQ1

- In process TCAD, interfaces are tracked using the level-set method
- A crucial step for the level-set method is the extension of the interface velocity to a narrow-band around the interface
- A parallel algorithm on a hierarchical grid has been implemented for shared memory systems

Tasks:

- Implement a new parallelization based on mesh decomposition / adaptive load balancing in the given C++ framework
- Compare it to the existing parallelization

- Programming in C++ under GNU/Linux
- OPENMP, Parallel programming



Dopant Diffusion in Process TCAD



Supervisor:

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Project AT1

- Control of doped regions is critical for every semiconductor device
- Dopants diffuse during implantation and annealing process steps prohibiting sharp doping profiles
- Coupling process and device TCAD (technology computer-aided design) provides the tools to predict the device characteristics of the final device

Tasks:

- Modeling dopant diffusion in 'hot' materials such as GaN, AlGaN, InP and SiGe
- Extending the diffusion framework of the commercial *Silvaco Victory Process* simulator
- Process and device Simulations of power and optoelectronic devices

- Programming in C/C++, Python
- Interest in solid state physics and/or semiconductor process and device engineering





Atomistic Modeling: Interaction of Oxide Defects with Electric Fields



Supervisor:

Dominic Waldhoer

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Project DW1

- Oxide defects in MOSFETs can act as charge trapping sites, causing various reliability issues like the Bias Temperature Instability (BTI)
- In our current BTI models the electric field across the gate oxide only affects the charge trapping levels of the defect
- However, the electric field can also interact with the charge distribution of the defect and potentially alter transition barriers between different defect states
- Density Functional Theory (DFT) allows us to simulate individual defects at an atomistic level and quantify these effects theoretically

Tasks:

- Use DFT to investigate the impact of electric fields on defect transition barriers due to dipole interaction
- Deduce a simplified model from your results which can be used in device simulators

Required knowledge:

- Solid understanding of electrodynamics and quantum mechanics
- Linux, Programming in Python



0.8

Atomistic Modeling: Extending the 4-State Defect Model



Supervisor:

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Project DW2

- Bias Temperature Instability (BTI) and Random Telegraph Noise (RTN) are caused by oxide defects which can trap/emit electric charges from/to the device substrate
- These defects are usually described by a 4-state Markov chain
- Although this 4-state model accounts for many experimental findings, it cannot explain certain observed defect behaviors like volatility or double capture/emission events
- *Density Functional Theory (DFT)* is an invaluable tool for the atomistic modeling of defects. DFT can be used to search for additional defect states and predict how these new states change the observable defect behavior

Tasks:

- Use DFT to identify possible defect states which can account for defect volatility and/or double capture/emission events
- Include these states in a Markov chain model and simulate the resulting RTN signals

- Solid understanding of physics
- Linux, Programming in Python





Web Interface to Control Defect Probing Instruments for Transistor Single-Defect Spectroscopy



Supervisor:

Michael Waltl

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Project MW1

- Electrical characterization of single defects in MOSFETs
- Use Defect Probing Instrument (right) developed at IuE
- Measurement sequences controlled by jobserver
- Jobserver communicates with SQL database

Tasks:

- Develop a web interface in Python (Django)
- Control of measurement flow
- Configuration of measurement tool
- Live tracking of measurement data

Requirements:

- Basic knowledge of Python
- Handling of UNIX operating system







Hardware- and Software Development for Defect Probing Instrument



Supervisor:

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Project MW2

- Electrical characterization of single defects in MOSFETs
- Defect Probing Instrument (right) developed at IuE
- Communicates with measurement host via USB interface

Tasks:

- Development of a calibration tool for DPI
- Development of a switching matrix
- Femto-ampere measurements
- Stepping motor controller and autofocus
- Enhancement of current control modul
- Application of zoom-and-scan method for single defect spectroscopy
- Driver development for general purpose measurement instruments (wafer prober, Keithleys, etc.)

Requirements:

- Knowledge of programming languages C/C++ and Python
- Profound knowledge of hardware development and PCB design





